

## WFP18N20-VB Datasheet

### N-Channel 200 V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	0.110 at $V_{GS} = 10$ V	30

#### FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC

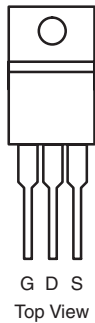


**RoHS**  
COMPLIANT

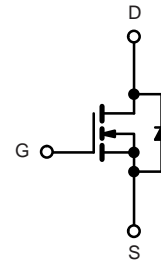
#### APPLICATIONS

- Primary Side Switch

TO-220AB



DRAIN connected to TAB



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	200	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	30	A
	T <sub>C</sub> = 125 °C		15	
Pulsed Drain Current		I <sub>DM</sub>	70	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	12	
Avalanche Current		I <sub>AS</sub>	12	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	20	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	126 <sup>b</sup>	W
	T <sub>A</sub> = 25 °C		3 <sup>a</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	15	°C/W
		Steady State	40	
Junction-to-Case (Drain)	$R_{thJC}$	0.85	1.1	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	200			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1		3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	40			A
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A		0.110	0.125	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A, T <sub>J</sub> = 125 °C		0.120	0.140	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A, T <sub>J</sub> = 175 °C		0.130	0.150	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3 A		0.132	0.152	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3 A		35		S
Dynamic <sup>a</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, F = 1 MHz		1800		pF
Output Capacitance	C <sub>oss</sub>			180		
Reverse Transfer Capacitance	C <sub>rss</sub>			80		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A		34	51	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			8		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			12		
Gate Resistance	R <sub>g</sub>		0.5		2.9	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 5.2 Ω I <sub>D</sub> ≅ 3 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 2.5 Ω		15	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			50	75	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			30	45	
Fall Time <sup>c</sup>	t <sub>f</sub>			60	90	
Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C)						
Pulsed Current	I <sub>SM</sub>				30	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 3 A, V <sub>GS</sub> = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 3 A, dI/dt = 100 A/μs		180	250	ns

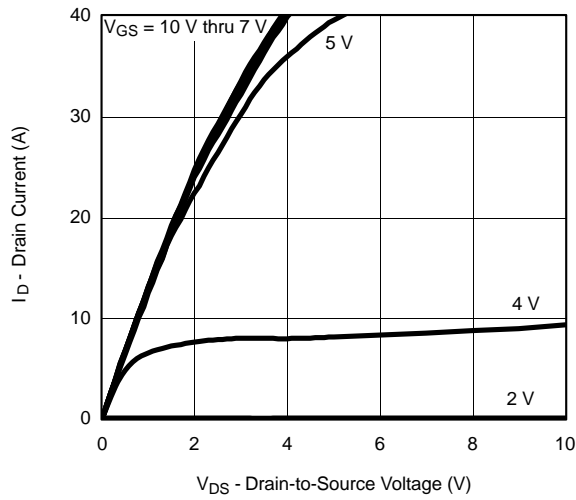
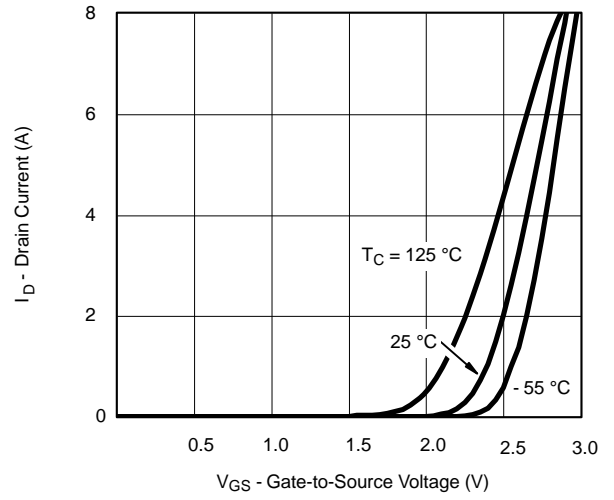
Notes:

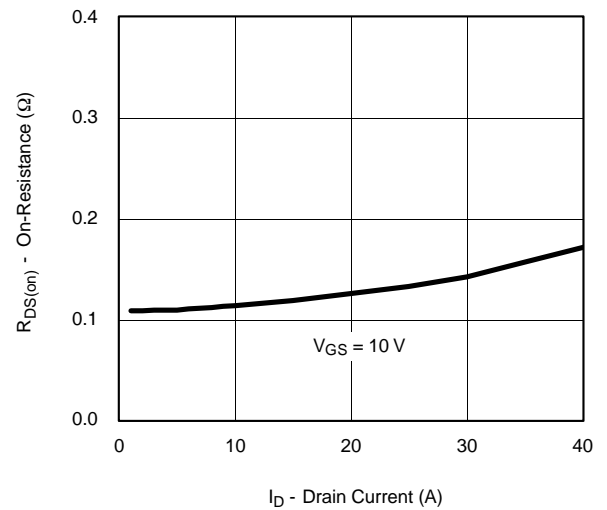
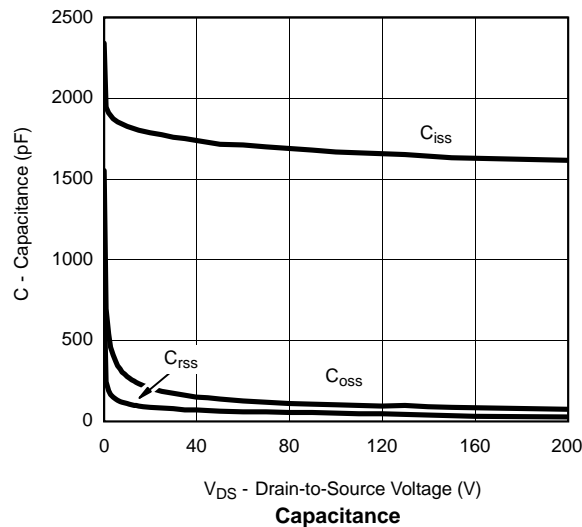
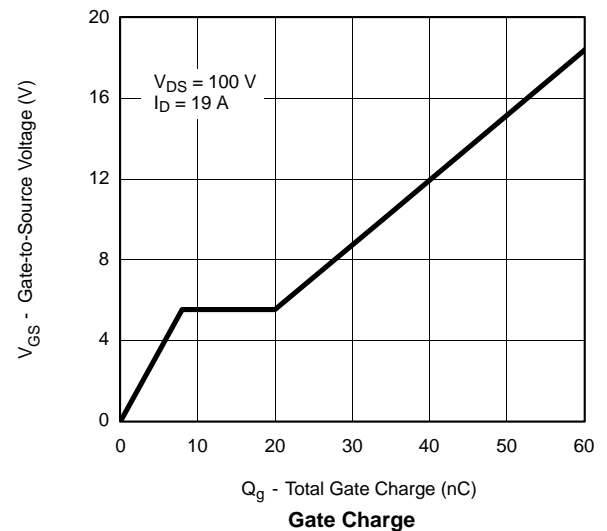
a. Guaranteed by design, not subject to production testing.

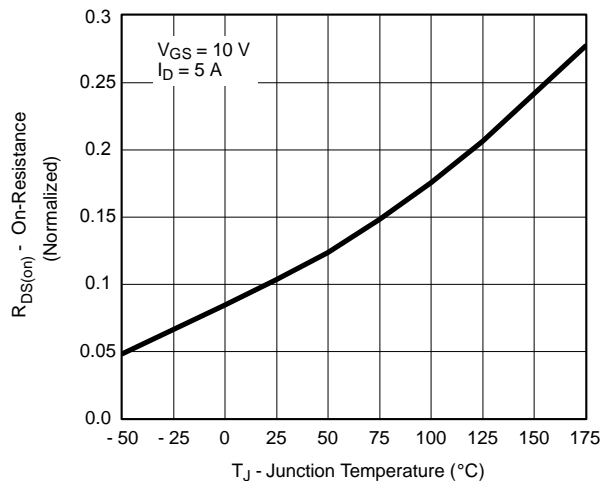
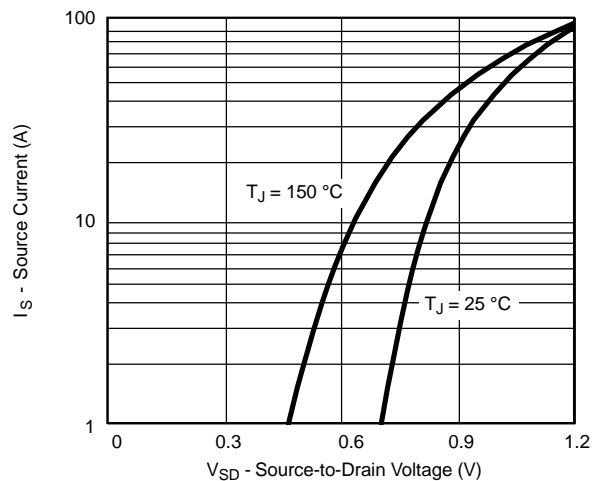
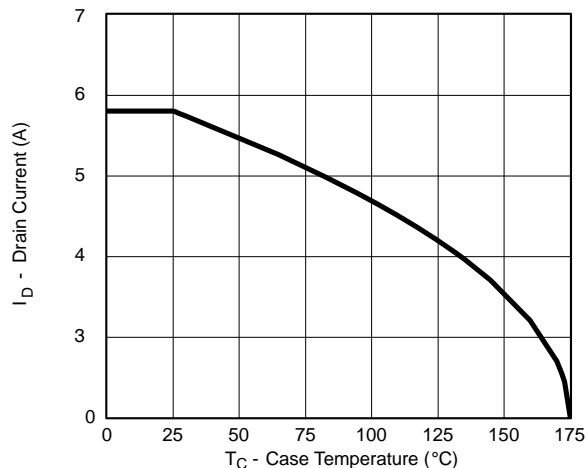
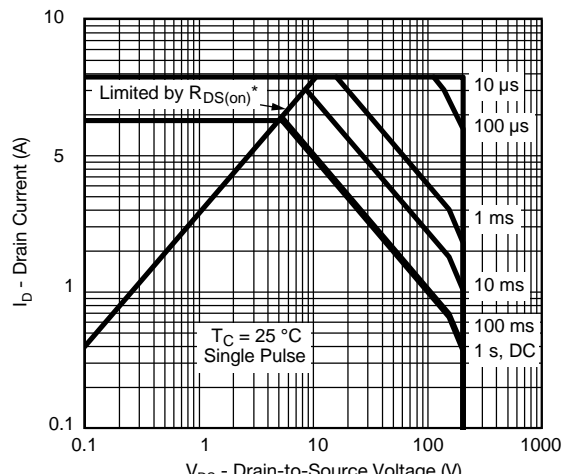
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

c. Independent of operating temperature.

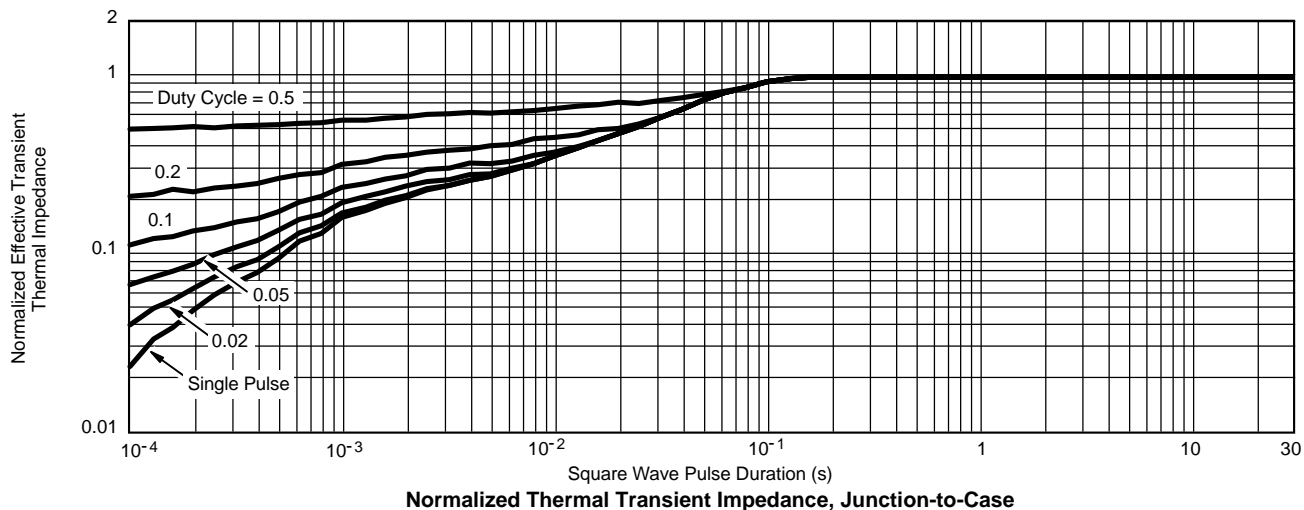
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

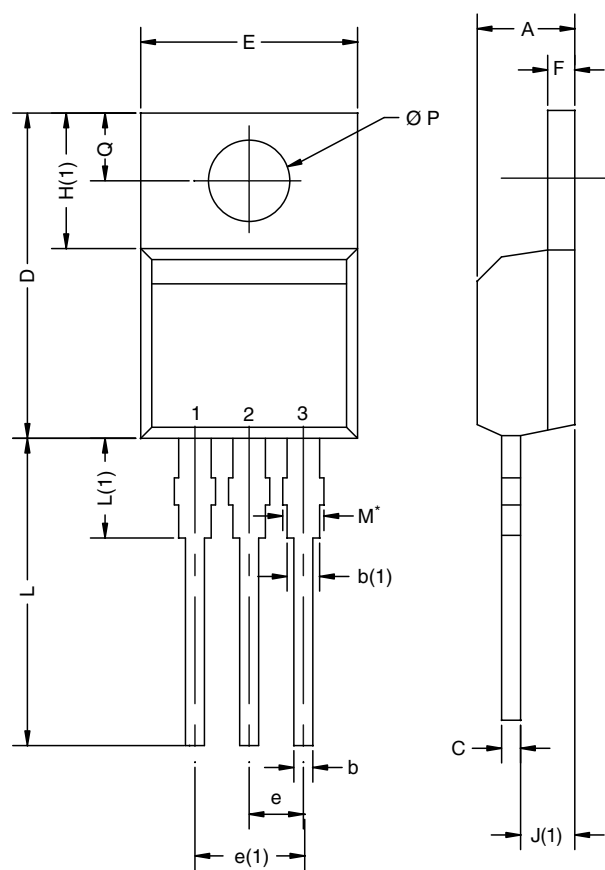
**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**
**THERMAL RATINGS**

**Maximum Avalanche Drain Current vs. Case Temperature**


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area**

**Normalized Thermal Transient Impedance, Junction-to-Case**

## TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

**Note**

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
 Heatsink hole for HVM

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